

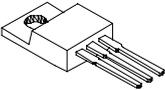
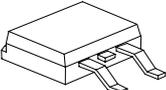
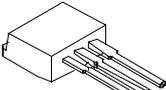
**MBR10150CT/MBRB10150CT/MBR10150CT-1**  
**SCHOTTKY RECTIFIER**

**Applications:**

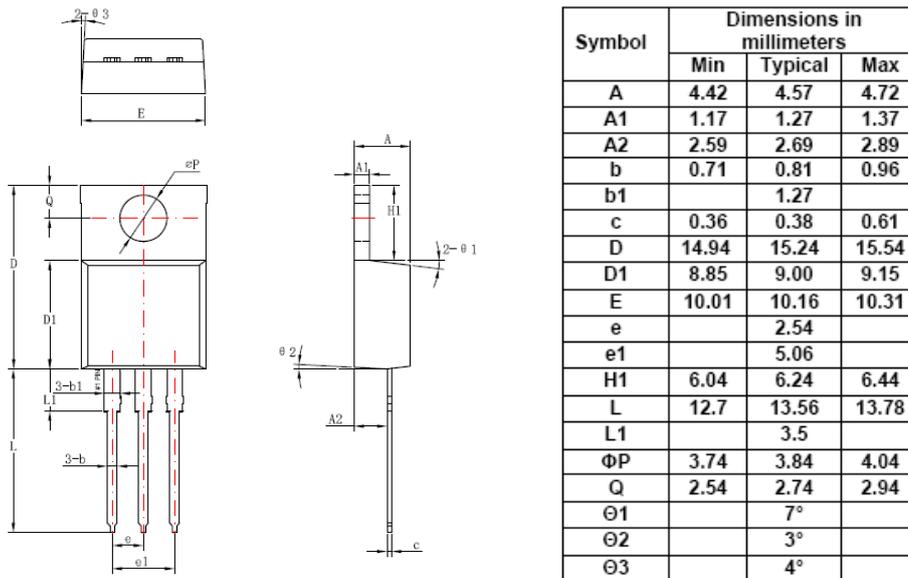
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

**Features:**

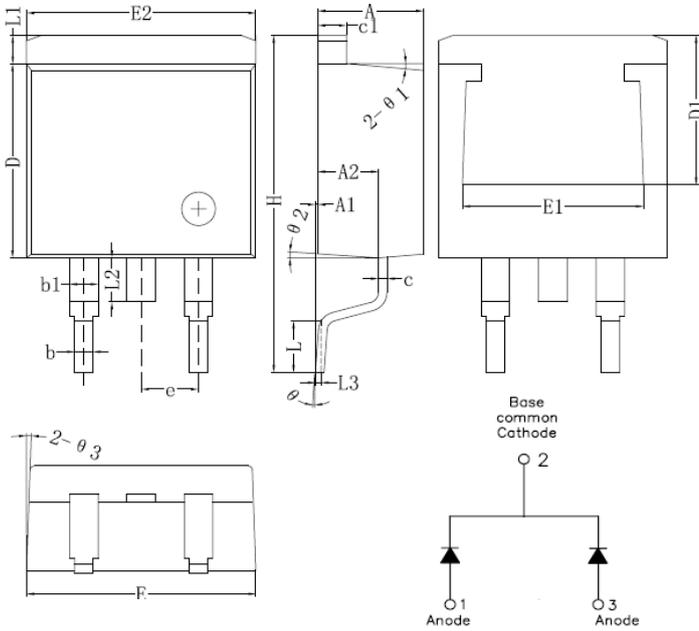
- 150 °C T<sub>J</sub> operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Case styles		
<b>MBR10150CT</b>  <b>TO-220AB</b>	<b>MBRB10150CT</b>  <b>D<sup>2</sup>PAK</b>	<b>MBR10150CT-1</b>  <b>TO-262</b>

**Mechanical Dimensions: In Inches / mm**

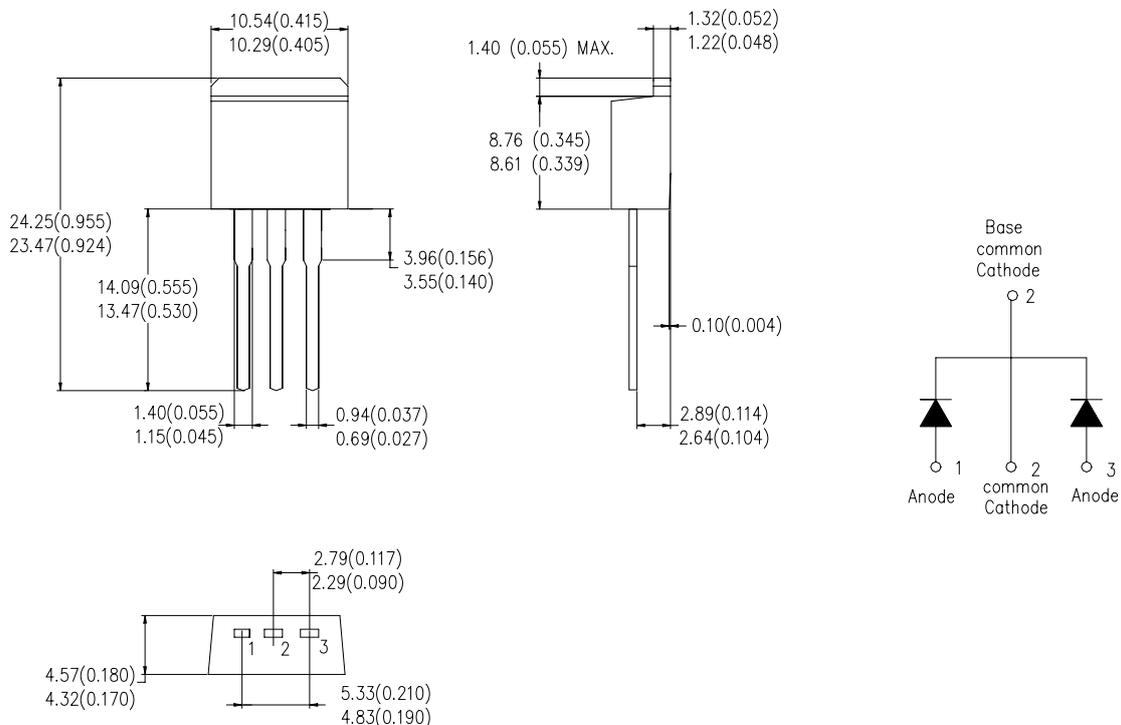


**TO-220AB**



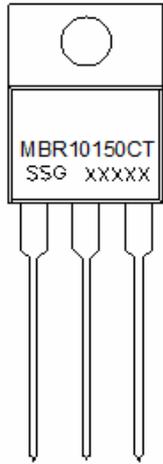
Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.55	4.70	4.85
A1	0	0.10	0.25
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
c1	1.17	1.27	1.37
D	8.55	8.70	8.85
D1	6.40		
E	10.01	10.16	10.31
E1	7.6		
E2	9.98	10.08	10.18
e		2.54	
H	14.6	15.1	15.6
L	2.00	2.30	2.70
L1	1.17	1.27	1.40
L2			2.20
L3		0.25BSC	
e	0	-	8°
e1		5°	
e2		4°	
e3		4°	

**D<sup>2</sup>PAK**

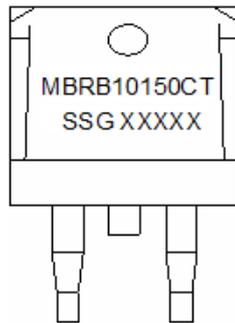


**TO-262**

**Marking Diagram:**



MBR10150CT



MBRB10150CT

Where XXXXX is YYWWL

MBR = Device Type  
 B = Package type  
 10 = Forward Current (10A)  
 150 = Reverse Voltage (150V)  
 CT/CT-1 = Configuration  
 SSG = SSG  
 YY = Year  
 WW = Week  
 L = Lot Number

**Cautions:** Molding resin  
 Epoxy resin UL:94V-0

**Ordering Information:**

Device	Package	Shipping
MBR10150CT	TO-220AB (Pb-Free)	50pcs / tube
MBRB10150CT	D <sup>2</sup> PAK (Pb-Free)	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

**Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	150	V
Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C=105^\circ\text{C}$ , rectangular wave form	10	A
Peak One Cycle Non-Repetitive Surge Current (per leg)	$I_{FSM}$	8.3 ms, half Sine pulse	138	A

**Electrical Characteristics:**

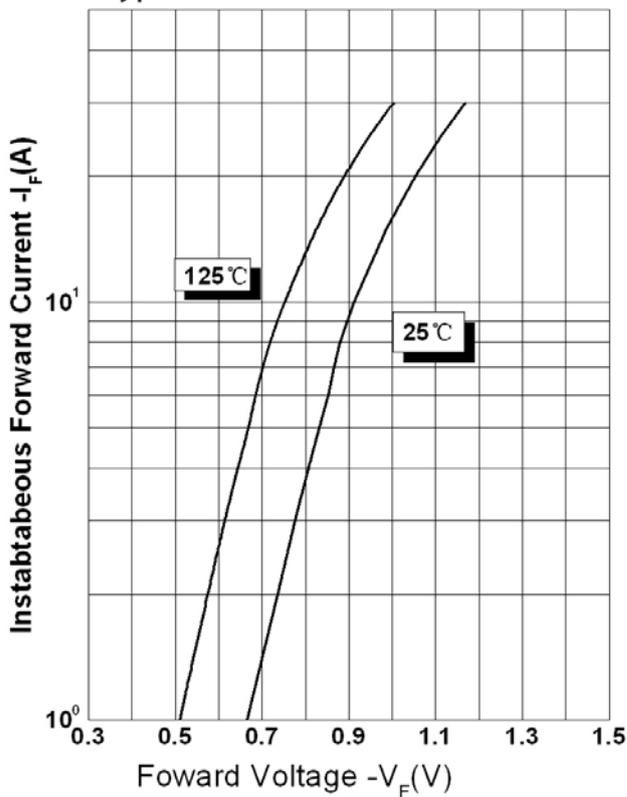
Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop(per leg)*	V <sub>F1</sub>	@ 5A, Pulse, T <sub>J</sub> = 25 °C	0.93	V
	V <sub>F2</sub>	@ 5A, Pulse, T <sub>J</sub> = 125 °C	0.73	V
Reverse Current (per leg)*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 25 °C	1.00	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 125 °C	7.0	mA
Junction Capacitance (per leg)	C <sub>T</sub>	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C f <sub>SIG</sub> = 1MHz	200	pF
Typical Series Inductance (per leg)	L <sub>S</sub>	Measured lead to lead 5 mm from package body	8.0	nH
Voltage Rate of Change	dv/dt	-	10,000	V/μs

\* Pulse Width < 300μs, Duty Cycle <2%

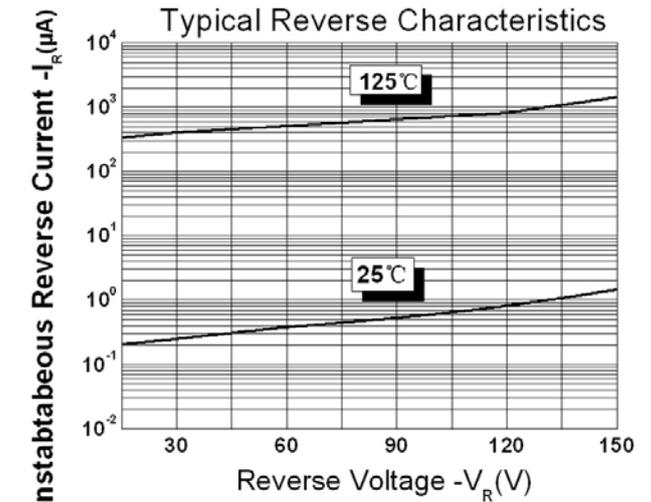
**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T <sub>J</sub>	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Maximum Thermal Resistance Junction to Case (per leg)	R <sub>θJC</sub>	DC operation	4.5	°C/W
Approximate Weight	wt	-	2/1.85	g
Case Style	TO-220AB D <sup>2</sup> PAK TO-262			

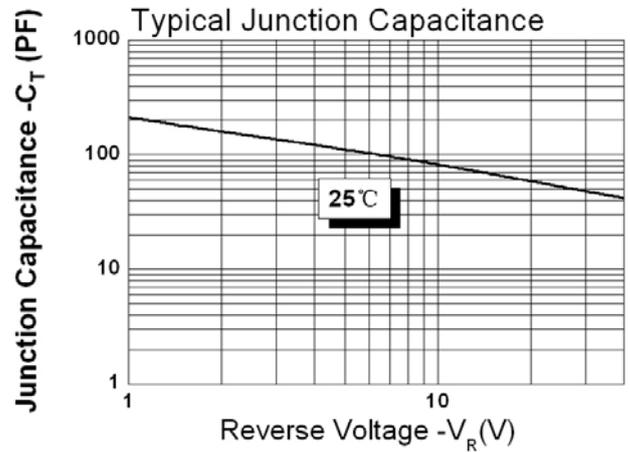
**Figure 1**  
Typical Forward Characteristics



**Figure 2**  
Typical Reverse Characteristics



**Figure 3**  
Typical Junction Capacitance



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